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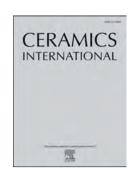
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Microwave dielectric properties, microstructure, and bond energy

of Zn<sub>3-x</sub>Co<sub>x</sub>B<sub>2</sub>O<sub>6</sub> low temperature fired ceramics

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#### **Abstract**

Low temperature co-fired ceramics (LTCCs) technology plays an important role in modern wireless communication.  $Zn_{3-x}Co_xB_2O_6$  (x=0–0.25) low temperature fired ceramics were synthesized via traditional solid-state reaction method. Influences of  $Co^{2+}$  substitution on crystal phase composition, grain size, grain morphology, microwave dielectric properties, bond energy, and bond valence were investigated in detail. X-ray diffraction analysis indicated that the major phase of the ceramics was monoclinic  $Zn_3(BO_3)_2$ . Solid solution was formed with  $Co^{2+}$  substituted for  $Zn^{2+}$  because no individual phase that contained Co was observed. An increase in the amount of  $Co^{2+}$  substitution changed average grain sizes, and regrowth of grains were observed with  $Co^{2+}$  substitution. Appropriate amount of  $Co^{2+}$  substitution improved densification. With changes in  $Co^{2+}$  substitution, bond energy of major phase and average bond valence of B-O were positively correlated to temperature coefficient of resonant frequency. The  $Zn_{2.927}Co_{0.075}B_2O_6$  ceramic sintered at 875 °C for 4 h exhibited excellent microwave properties with  $\varepsilon_r$ =6.79, Q×f=140402 GHz, and  $\tau_f$ =-87.42 ppm/°C. This ceramic is regarded as candidate for LTCC applications.

**Keywords:** Microwave dielectric properties; LTCC; microstructure; bond energy

#### 1. Introduction

Microwave dielectric ceramics are indispensable in the development of wireless communication; specifically, these ceramics are commonly used as resonators and capacitors [1]-3]. With further development in wireless communication, new demands have been proposed for microwave dielectric ceramics: miniaturization, multifunction, high reliability, and low dielectric loss at high frequency. Low temperature co-fired ceramics (LTCCs) and corresponding technologies that meet these demands, are also beneficial for radio frequency (RF) microwave and millimeter-wave circuits [4]. LTCCs are used to package passive and active components into multilayer structures to achieve the characteristics of miniaturization and multifunction. Ag is usually used as an electrode in the LTCC multilayer because of its low conductor loss and low cost. To co-fire a ceramic with Ag, the sintering temperature of the ceramic must usually be below 950 °C. A low relative dielectric constant ( $\varepsilon_r$ ) is required for LTCCs in substrate applications because the relationship between  $\varepsilon_r$  and propagation delay time  $(T_d)$  is:  $T_d = L\sqrt{\varepsilon_r/c}$  [5], where L is the traveling distance of the signal and c is the speed of light. Low dielectric loss of LTCCs is an important feature and it is related to high efficiency and low noise in devices [6]. Moreover, the temperature coefficient of the resonant frequency  $(\tau_f)$  of LTCCs is a measure of the temperature stability of the resonant frequency, which is required near zero for practical applications.

Not every microwave dielectric ceramic is suitable for LTCC technology. For example, the densification temperature is as high as 1340 °C for Zn<sub>2</sub>SiO<sub>4</sub> [7] and 1400 °C for Mg<sub>2</sub>SiO<sub>4</sub> [8], and these sintering temperatures are extremely high for LTCC applications. Glasses, oxides, and fluorides, which have low melting points, are usually used as sintering aids to reduce the sintering temperature of these ceramics with low

dielectric loss [6],9],10]. Furthermore, ceramics without sintering aids, such as  $Sr_2NaMg_2V_3O_{12}$ ,  $La_2Zr_3(MoO_4)_9$ , and  $LiNiPO_4$ , have also been investigated in recent years [11]–13]. Wu et al.[14] first reported the microwave dielectric properties of the  $Zn_3B_2O_6$  ceramic sintered at 925 °C for 4 h:  $\varepsilon$ ,=6.7,  $Q\times f$ =58500 GHz, and  $\tau_f$ =-58 ppm/°C.  $Zn_3B_2O_6$  has an innate low sintering temperature and excellent microwave dielectric properties, and thus, it is suitable for LTCC applications. Previous research has reported that  $Co^{2+}$  substitution is an efficient means of increasing relative density and  $Q\times f$ , and decreasing sintering temperature[15]–18]. Moreover, the effective radius of  $Zn^{2+}$  is 0.60 Å, and that of  $Co^{2+}$  is 0.58 Å when their coordination number (CN) is 4 [19].

On the basis of the above information,  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics without sintering aids were synthesized via the solid-state reaction method in this work. The influences of substituting  $Co^{2+}$  for  $Zn^{2+}$  on crystal phase, microstructure, densification, and microwave dielectric properties of  $Zn_{3-x}Co_xB_2O_6$  ceramics were investigated. The relationship between crystal phase, microstructure, densification, bond energy, bond valence, and microwave dielectric properties of  $Zn_{3-x}Co_xB_2O_6$  ceramics were investigated in detail.

## 2. Experimental procedure

Samples of Zn<sub>3-x</sub>Co<sub>x</sub>B<sub>2</sub>O<sub>6</sub> (*x*=0–0.25) ceramics were prepared via the solid-state reaction method. Analytically pure ZnO (99.0%, Ke Long chemical factory in China), CoO (99.0%, Ke Long chemical factory in China), and H<sub>3</sub>BO<sub>3</sub> (99.5%, Ke Long chemical factory in China) were used as raw materials. The loss of B<sub>2</sub>O<sub>3</sub> during calcination was compensated for 12 wt.% excess H<sub>3</sub>BO<sub>3</sub> in the first step of weighing the raw material [14]. The mixtures were weighted according to the compositions and

milled with deionized water and zirconia balls in nylon containers for 4 h. The mixed slurries were then dried in an oven respectively and then calcined at 875 °C for 4 h. The calcined materials were remilled for 4 h. The wet materials were dried and mixed with polyvinyl alcohol binder (12 wt.%). Samples were then pressed into cylinders with 12 mm in diameter and 6 mm in height at 100 MPa. The raw cylinders were sintered at 850-900 °C for 4 h to obtain the final samples that were used for subsequent tests.

Crystal phases of the ceramics were identified via a X-ray diffractometer (Rigaku MinFlex 600) with a scanning speed of 4°/min. Crystal structure parameters of the samples were obtained via refinements of X-ray diffraction (XRD) data using FullProf software. The bond energy and bond valence were calculated from the refined XRD data. A scanning electron microscope (SEM: JEOL JSM-6490LV) with an acceleration voltage of 20 kV, was used to observe grain sizes and microstructure of the sintered ceramics. Archimedes' method was used to measure bulk densities of the samples. Microwave dielectric properties of the ceramics were measured via the Hakki-Coleman dielectric resonator method using a vector network analyzer (Agilent Technologies, N5230A, 300 kHz~20 GHz) [20]. The temperature coefficient of the resonant frequency ( $\tau_i$ ) was determined using Equation (1):

$$\tau_f = \frac{f_2 - f_1}{f_1(T_2 - T_1)} \times 10^6 \,(\text{ppm/°C}) \tag{1}$$

where  $f_1$  and  $f_2$  are the resonant frequencies measured at temperatures  $T_1$  and  $T_2$ , respectively.

## 3. Results and discussion

#### Fig. 1

The  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 875 °C present a major phase ( $Zn_3(BO_3)_2$ , ICSD #14240) and a minor phase ( $Zn_4O(B_6O_{12})$ , ICSD #34085), as shown

in Fig. 1(a). The standard XRD patterns of the two phases are based on the ICSD data and their curves are calculated using Mercury software. The main diffraction peaks are in the range of  $20^{\circ}$ - $50^{\circ}$ , and some of the indexes of diffraction are labeled in Fig. 1. Substituting  $Co^{2+}$  for  $Zn^{2+}$  did not introduce any new phase containing Co, and this fact indicated that  $Co^{2+}$  replaced the position of  $Zn^{2+}$  and formed a solid solution in  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics. The similarity in the values of the effective ion radii of  $Zn^{2+}$  and  $Co^{2+}$  was the necessary condition for forming the solid solution. In addition, the diffraction peak (211) of the minor phase is not observed until substitution of  $Co^{2+}$  is increased to 0.15 mole, as seen in Fig. 1(b), and this demonstrated that  $Zn_3(BO_3)_2$  formed a solid solution with  $Zn_4O(B_6O_{12})$  when x<0.075 and that further substitution of  $Co^{2+}$  reduced the compatibility on structure between the two phases. The intensity of the diffraction peak (310) of the minor phase is stable, as seen in Fig. 1(c), and this indicated that  $Co^{2+}$  substitution did not obviously change the weight percentage of the  $Zn_4O(B_6O_{12})$  phase in the samples.

## Fig. 2

XRD patterns were refined using FullProf software with the Rietveld method [21]. Characteristics of the crystal structure, lattice parameters (a, b, c), and volume of the unit cell (Vc) were obtained from the refinements of  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 875 °C. Monoclinic structure with the space group of I 1 2/c 1 for  $Zn_3(BO_3)_2$  and cubic structure with the space group of I -4 3 m for  $Zn_4O(B_6O_{12})$  were used as models for XRD refinements. Details of the models were based on the standard PDF cards ICSD #14240 and ICSD #34085. Moreover,  $\alpha$ = $\gamma$ =90° in the monoclinic structure. And  $\alpha$ =b=c,  $\alpha$ = $\beta$ = $\gamma$ =90° in the cubic structure. The results of the XRD refinements can be seen in Fig. 2 and the refinements are summarized in Table 1. The values of  $\chi^2$  were

less than 2, which showed that the refinements were reliable. The lattice parameters changed slightly with an increase in  $Co^{2+}$  substitution, and this indicated that  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 875 °C were stable on the structure. Furthermore, the weight percentages of  $Zn_3(BO_3)_2$  and  $Zn_4O(B_6O_{12})$  changed with a change in x, and the weight percentage of  $Zn_4O(B_6O_{12})$  was maximized at x=0.075.

#### Fig. 3

The crystal structure of the major phase  $(Zn_3(BO_3)_2)$  is shown in Fig. 3; this was obtained from the result of XRD refinement for the  $Zn_{2.925}Co_{0.075}B_2O_6$  ceramic, which was sintered at 875 °C. In this sample, the unit cell of monoclinic phase  $Zn_3(BO_3)_2$  included 8 molecules of  $Zn_3B_2O_6$ , with  $\beta$ =97.40376°, a=23.44124 Å, b=5.04233 Å, and c=8.38215 Å.  $Zn^{2+}$ ,  $B^{3+}$ , and  $O^{2-}$  formed tetrahedral  $[ZnO_4]$  and triangular  $[BO_3]$  connected though the vertex  $O^{2-}$ . Moreover, on the basis of the principle of charge conservation, one  $O^{2+}$  connected one triangle of  $[BO_3]$  and two tetrahedra of  $[ZnO_4]$  in the crystal phase  $Zn_3(BO_3)_2$ . In a practical sample, because some  $Co^{2+}$  was substituted for  $Zn^{2+}$ ,  $Co^{2+}$  replaced some of  $Zn^{2+}$  in the crystal structure. The crystal structure remained stable even when the amount of substitution reached to 0.25 mole, as seen from the analysis of the XRD patterns.

Fig. 4

#### Fig. 5

Microstructure and grain morphology of the ceramics are related to the microwave dielectric properties [23]. The microstructure, grain size, and grain morphology of  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 875 °C were observed via SEM, as seen in Fig. 4. The average grain sizes and their standard deviations are showed in Fig. 5. Grain boundaries of all samples were apparent, but the morphology of the grains

changed with an increase in  $Co^{2+}$  substitution. With an increase in  $Co^{2+}$  substitution from 0 mole to 0.05 mole, the grains of the ceramics regrew, as seen in Fig. 4(a)-(c). The morphology of the grains changed obviously; specifically, some irregular grains appeared in the range of  $0.025 \le x \le 0.05$ . Thus, it could be concluded that substituting an appropriate amount of  $Co^{2+}$  for  $Zn^{2+}$  promoted the regrowth of grains in  $Zn_{3-x}Co_xB_2O_6$  ceramics. Furthermore, the average grain size decreased from 3.79  $\mu$ m at x=0 to 2.77  $\mu$ m at x=0.05, and the decrease in the corresponding standard deviation of grain size also supported this conclusion. The grain morphology became regular again, and grains grew closely when x reached 0.075, as seen in Fig. 4(d). With a further increase in the amount of  $Co^{2+}$  substitution to 0.25 mole, the average grain size increased to 4.08  $\mu$ m, and their grain boundaries tended to be blurry.

The bulk density and relative density of the samples are shown in Fig. 6. The theoretical density of  $Zn_{3-x}Co_xB_2O_6$  (x=0–0.25) ceramics was assumed to be equal for samples at different sintering temperatures. Moreover, the theoretical density ( $\rho_{th}$ ) and relative density ( $\rho_r$ ) of the samples were calculated using Equations (2) and (3), as shown below:

$$\rho_{th} = \frac{ZA}{V_c N_A},\tag{2}$$

$$\rho_r = \frac{\sum w_i}{\sum_{\rho_i}^{w_i}},\tag{3}$$

where  $N_A$ ,  $V_c$ , A, and Z are the Avogadro's constant (mol<sup>-1</sup>), the volume of unit cell, the molar molecular weight (g/mol), and the number of molecules in a unit cell, respectively. Also,  $w_i$  and  $\rho_i$  were the weight percentage and theoretical density of phase i respectively. Values of  $V_c$  were derived from the results of XRD refinements. Bulk

densities of the samples varied between 3.785 g/cm<sup>3</sup> and 4.067 g/cm<sup>3</sup>, and relative densities varied between 89.98% and 95.98%. The densest sample was the  $Zn_{2.925}Co_{0.075}B_2O_6$  ceramic sintered at 875 °C, with a bulk density of 4.067 g/cm<sup>3</sup> and relative density of 95.98%. The variations in bulk density and relative density were similar because of their similar values of the theoretical density of  $Zn_{3-x}Co_xB_2O_6$  ceramics with different values of x. The relationship between porosity (P) and relative density ( $\rho_r$ ) is  $P=1-\rho_r$ . As seen in Fig. 6(b), an optimal amount of substituted  $Co^{2+}$  enabled the ceramics to reach maximal relative density, and the optimal amount varied at different sintering temperatures. Higher sintering temperature corresponded to a smaller optimal amount of substituted  $Co^{2+}$  for  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 850-900 °C. This phenomenon indicated that an appropriate amount of  $Co^{2+}$  substitution reduced porosity of the ceramics subjected to the same sintering temperature, and this influence increased when the sintering temperature was higher.

#### Fig. 7

Relative dielectric constants ( $\varepsilon_r$ ) of ceramics mainly depend on crystal phase composition and porosity [24]-25].  $\varepsilon_r$  values of  $Zn_{3-x}Co_xB_2O_6$  (x=0–0.25) ceramics sintered at 850-900 °C are shown in Fig. 7(a). Phase compositions of  $Zn_{3-x}Co_xB_2O_6$  (x=0–0.25) ceramics sintered at 875 °C could be observed from the results of XRD refinements; the weight percentages of the major phase and minor phase were slightly changed. In this situation, changes in the weight percentage of the phase composition were not the dominant factor that influenced changes in  $\varepsilon_r$ . Furthermore, the same changes were observed between the relative density and  $\varepsilon_r$ . Therefore, values of  $\varepsilon_r$  for  $Zn_{3-x}Co_xB_2O_6$  ceramics were mainly influenced by relative density or porosity. The value of  $\varepsilon_r$  for the densest  $Zn_{2.925}Co_{0.075}B_2O_6$  ceramic sintered at 875 °C was 6.79.

Equation (4) was used to calculated the value of  $\varepsilon_r$  for the pure ceramic without porosity [25]:

$$\varepsilon_{\rm r} = \varepsilon_{\rm m} \left( 1 - \frac{3P(\varepsilon_{\rm m} - 1)}{2\varepsilon_{\rm m} + 1} \right) \tag{4}$$

where  $\varepsilon_r$ , P, and  $\varepsilon_m$  are the measured relative dielectric constant, fractional porosity, and calculated  $\varepsilon_r$  value of the pure ceramic respectively. The value of  $\varepsilon_r$  for the pure  $Zn_{2.925}Co_{0.075}B_2O_6$  ceramic sintered at 875 °C was calculated to be 7.14.

Dielectric loss of microwave dielectric ceramics is related to intrinsic loss (such as phase composition and crystal structure) and extrinsic loss (such as porosity and phase crystallization) [26],27].  $Q \times f$  was used to measure dielectric loss of the ceramics, and the results are shown in Fig. 7(b). Relative density showed the same variation with  $Q \times f$ for  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics, and this fact indicated that porosity was the dominant factor that influenced dielectric loss of the ceramics. In other words, an appropriate amount of Co2+ substitution enhanced densification and reduced the dielectric loss of the  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics.  $Q\times f$  value of the Zn<sub>2,925</sub>Co<sub>0,075</sub>B<sub>2</sub>O<sub>6</sub> ceramic sintered at 875 °C was much larger than that of the other samples sintered at the same temperature. This phenomenon might contribute to the phase composition and corresponding crystal structure. As discussed regarding the XRD patterns shown in Fig. 1(a),  $Zn_3(BO_3)_2$  formed a solid solution with  $Zn_4O(B_6O_{12})$  when  $x \le 0.075$ , and further Co<sup>2+</sup> substitution reduced their compatibility on the structure. The Zn<sub>2.925</sub>Co<sub>0.075</sub>B<sub>2</sub>O<sub>6</sub> ceramic sintered at 875 °C contained the maximal weight percentage of Zn<sub>4</sub>O(B<sub>6</sub>O<sub>12</sub>), and there was complete compatibility on the structure between the two phases. Therefore, the compatibility on the crystal structure and high densification increased the  $Q \times f$  to 140402 GHz for the  $Zn_{2.925}Co_{0.075}B_2O_6$  ceramic sintered at 875 °C.

 $Zn_3(BO_3)_2$  was the major phase in  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics. Total bond

energy of the  $Zn_3(BO_3)_2$  phase in  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 875 °C was calculated strictly according to the theory of Sanderson [28],29]. All data used to calculated the bond energy could be found in Ref. [29] and Table 2. Bond energy ( $E_b$ ) of a single bond contains nonpolar covalent bond energy ( $E_c$ ) and polar covalent bond energy ( $E_i$ ):

$$E_b = t_c E_c + t_i E_i \tag{5}$$

$$1 = t_c + t_i \tag{6}$$

where  $t_c$ , and  $t_i$  are the covalent and ionic blending coefficients respectively. The partial charges of the atoms that constitute the chemical bond were used to calculate the value of  $t_i$  according to the following equation:

$$t_i = \frac{|C_{PA} - C_{PB}|}{2} \tag{7}$$

where  $C_{PA}$  and  $C_{PB}$  are the partial charges of atoms A and B respectively. The electronegativity of the molecule and atoms that constituted the chemical bond were used to calculate the partial charge according to the following equation:

$$C_{Pi} = \frac{S_m - S_i}{\Delta S_i} \tag{8}$$

where  $C_{Pi}$ ,  $S_m$ , and  $S_i$  are the partial charge of atom i, electronegativity of the molecule that contains the chemical bond, and the electronegativity of atom i respectively. Polyhedra of  $[Zn(1)O_4]$ ,  $[Zn(2)O_4]$ ,  $[Zn(3)O_4]$ ,  $[B(1)O_3]$ , and  $[B(2)O_3]$  were considered to be 5 styles of molecules that formed the  $Zn_3(BO_3)_2$  phase.  $\Delta S_i$  is the change in the complete loss of an electron.  $S_m$  is simply the geometric mean of the electronegativity of all the atoms that constitute the molecule, and it was calculated using the following Equation:

$$S_m = \sqrt[n]{\prod_{j=1}^n S_j} \tag{9}$$

where  $S_j$  is the electronegativity of atom j, and n is the number of atoms that form the molecule. Moreover,  $E_c$  and  $E_i$  were calculated using Equations (10) and (11):

$$E_i = \frac{33200}{R_0} \tag{10}$$

$$E_c = \frac{(R_A + R_B)(E_{A-A}E_{B-B})^{1/2}}{R_o} \tag{11}$$

where  $R_o$ ,  $R_A$ , and  $R_B$  are respectively the bond length between atoms A and B, nonpolar covalent radii of atom A, and nonpolar covalent radii of atom B. Bond length (pm) corresponds to  $E_i$  in kcal/mol.  $E_{A-A}$  and  $E_{B-B}$  are defined as homonuclear bond energies of atom A and B, respectively. Particularly,  $E_{Zn-Zn}$ =35.8 kcal/mol,  $E_{B-B}$ =76.7 kcal/mol,  $E_{O-O}$ =104 kcal/mol. The bond energy of a polyhedra is the sum of the bond energies of all of the individual bonds that form the polyhedra. Furthermore, the total bond energies of the  $Zn_3(BO_3)_2$  phase, that is, the total energies of the five types of polyhedra in  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics, were calculated to compare with the value of  $\tau_f$ , as seen in Fig. 8.

It has been observed in previous research that bond valence was related to  $\tau_f$  [9],30]. [BO<sub>3</sub>] triangles are the basic framework in Zn<sub>3-x</sub>Co<sub>x</sub>B<sub>2</sub>O<sub>6</sub> (x=0–0.25) ceramics. Therefore, the average bond valence of B-O was calculated using Equations (12) and (13) [31]:

$$d_{ij} = R_{ij} - b \ln v_{ij} \tag{12}$$

$$V_a = \frac{\sum v_{ij}}{n} \tag{13}$$

where  $d_{ij}$ ,  $R_{ij}$ , and  $v_{ij}$  are the bond length between atoms i and j, bond valence parameter, bond valence of atoms i and j, respectively.  $V_a$  is the average bond valence, and n is the number of bonds included in the calculation. According to Ref. [31], b=0.37 Å, and

 $R_{B-O}$ =1.37 Å. There were six types of B-O bonds in  $Zn_3(BO_3)_2$ , and bond length values are shown in Table 2. The average bond valence of B-O was simply the average of the six types of B-O bond valence. Calculated average bond valences of B-O for the  $Zn_3(BO_3)_2$  phase in  $Zn_{3-x}Co_xB_2O_6$  ceramics sintered at 875 °C are shown in Fig. 8.

The value of  $\tau_f$  is mainly influenced by phase composition, the linear expansion coefficient ( $\alpha$ ), and the temperature coefficient of the dielectric constant ( $\alpha_{\varepsilon}$ ) [22],23]:

$$\tau_f = -(\alpha + \frac{1}{2}\alpha_{\varepsilon}) \tag{14}$$

Bond energy is related to the stability of the crystal structure of the ceramics, and therefore, bond energy is related to  $\tau_f$ . B-site bond valence is related to the temperature coefficient of the dielectric constant, and according to Equation (14), B-site bond valence is related to  $\tau_f$  [17]. Phase composition was obtained from results of XRD refinements. There was no obviously relationship between the percentage of the  $Zn_4O(B_6O_{12})$  phase and the value of  $\tau_f$  due to the slight change in the phase composition. Moreover, bond energy of Zn<sub>3</sub>(BO<sub>3</sub>)<sub>2</sub> and average bond valence of B-O triangles were observed to be positively correlated to  $\tau_f$ , as shown in Fig. 8. Therefore, the major phase  $Zn_3(BO_3)_2$  determined  $\tau_f$  values of the  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics.  $\tau_f$  values of the Zn<sub>3-x</sub>Co<sub>x</sub>B<sub>2</sub>O<sub>6</sub> ceramics sintered at 875 °C varied from -62.49ppm/°C to -87.42ppm/°C. An appropriate amount of Co<sup>2+</sup> substitution reduced the bond energy of  $Zn_3(BO_3)_2$  to 8146 kJ/mol at x=0.075, and also resulted in a relatively large negative value of  $\tau_f$  (-87.42 ppm/°C), and this indicated that low bond energy corresponded to low stability on the structure of the ceramics. Similarly, the conclusion that smaller average bond valence of B-O corresponded to larger negative  $\tau_f$  for Zn<sub>3-x</sub>Co<sub>x</sub>B<sub>2</sub>O<sub>6</sub> ceramics sintered at 875 °C was made. Furthermore,  $\tau_f$  should be near zero for practical application, and some methods for adjusting  $\tau_f$  have been investigated. These methods

included substituting ions ( $Cu^{2+}$ , $Ti^{4+}$ ) [27],32] or compensating with other materials that have large positive values of  $\tau_f$  [21],33].

## 4. Conclusions

 $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 850-900 °C were prepared via the traditional solid-state reaction method. A major phase  $Zn_3(BO_3)_2$  and minor phase  $Zn_4O(B_6O_{12})$  constituted the crystal phase of the ceramics.  $Co^{2+}$  substitution promoted the regrowth of grains and changes in grain size. An appropriate amount of  $Co^{2+}$  substitution increased relative density and reduced dielectric loss. The  $Zn_{2.925}Co_{0.075}B_2O_6$  ceramic sintered at 875 °C was the densest sample. The value of  $Q\times f$  was closely related to relative density, phase composition, and crystal structure. Bond energy of  $Zn_3(BO_3)_2$  and average bond valence of B-O were calculated and presented a positive correlation with  $\tau_f$ . The  $Zn_{2.927}Co_{0.075}B_2O_6$  ceramic sintered at 875 °C for 4 h exhibited excellent microwave properties with  $\varepsilon_f$ =6.79,  $Q\times f$ =140402 GHz, and  $\tau_f$ =-87.42 ppm/°C. Thus, the ceramic was regarded as a potential LTCC material.

## Acknowledgements

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## **Figure captions:**

Fig. 1 (a) XRD patterns of  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 875 °C, (b) amplified figure at  $2\theta = 28.5^{\circ} - 30.5^{\circ}$ , (c) amplified figure at  $2\theta = 36.5^{\circ} - 39^{\circ}$ .

Fig. 2 Rietveld refinements of  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 875 °C, (a) x = 0, (b) x = 0.025, (c) x = 0.05, (d) x = 0.075, (e) x = 0.15, (f) x = 0.25.

Fig. 3 The crystal structure of a unite cell of Zn<sub>3</sub>(BO<sub>3</sub>)<sub>2</sub>.

Fig. 4 SEM photographs of  $Zn_{3-x}Co_xB_2O_6$  (x=0–0.25) ceramics sintered at 875 °C, (a) x = 0, (b) x = 0.025, (c) x = 0.05, (d) x = 0.075, (e) x = 0.15, (f) x = 0.25.

Fig. 5 Statistics of grain sizes of  $Zn_{3-x}Co_xB_2O_6$  (x=0-0.25) ceramics sintered at 875 °C, (a) x = 0, (b) x = 0.025, (c) x = 0.05, (d) x = 0.075, (e) x = 0.15, (f) x = 0.25.

Fig. 6 Densification characteristic of  $Zn_{3-x}Co_xB_2O_6$  (x=0–0.25) ceramics sintered at 850–900 °C, (a) bulk density, (b) relative density.

Fig. 7 Microwave dielectric properties of  $Zn_{3-x}Co_xB_2O_6$  (x=0–0.25) ceramics sintered at 850–900 °C, (a)  $\varepsilon_r$ , (b)  $Q\times f$ , (c)  $\tau_f$ .

Fig. 8 Bond energies of  $Zn_3(BO_3)_2$  and average bond valences of B-O contrast to  $\tau_f$  of  $Zn_{3-x}Co_xB_2O_6$  (x = 0 - 0.25) ceramics sintered at 875 °C

## **Table captions:**

Table 1 Parameters of structure and agreement factors of refinements for  $Zn_{3-x}Co_xB_2O_6$  (x=0–0.25) ceramics sintered at 875 °C.

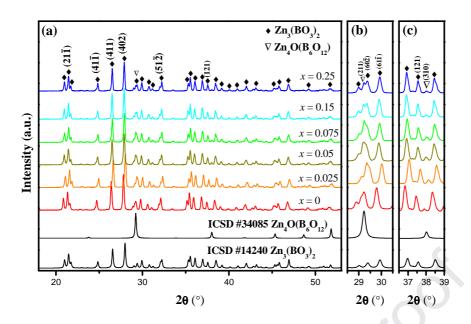
Table 2 Bond lengths of  $Zn_3(BO_3)_2$  from XRD refinements for  $Zn_{3-x}Co_xB_2O_6$  (x=0–0.25) ceramics sintered at 875 °C.

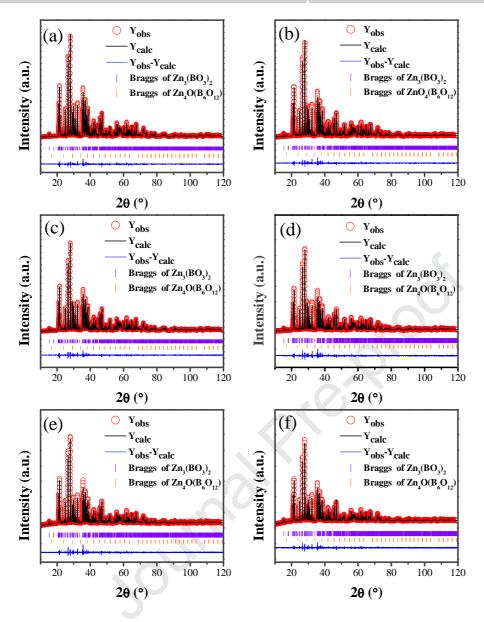
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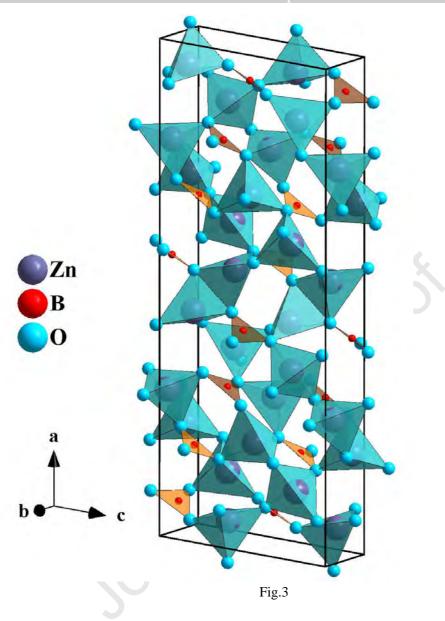
|                    |                         | x = 0    | x = 0.025 | x = 0.05 | x = 0.075 | x = 0.15 | x = 0.25 |
|--------------------|-------------------------|----------|-----------|----------|-----------|----------|----------|
|                    | a (Å)                   | 23.43185 | 23.46057  | 23.44825 | 23.44124  | 23.43675 | 23.44434 |
|                    | b (Å)                   | 5.03966  | 5.04576   | 5.04287  | 5.04233   | 5.04404  | 5.04966  |
|                    | c (Å)                   | 8.37482  | 8.38577   | 8.38231  | 8.38215   | 8.38755  | 8.39991  |
| $Zn_3B_2O_6$       | $\beta$ (Å)             | 97.43457 | 97.41837  | 97.40679 | 97.40376  | 97.39304 | 97.38065 |
|                    | $V_c$ (Å <sup>3</sup> ) | 980.656  | 984.369   | 982.909  | 982.496   | 983.299  | 986.191  |
|                    | wt. (%)                 | 96.53    | 93.59     | 93.61    | 92.30     | 95.69    | 94.59    |
|                    | a (Å)                   | 7.46698  | 7.47719   | 7.47365  | 7.47241   | 7.47516  | 7.47669  |
| $Zn_4O(B_2O_{16})$ | $V_c$ (Å <sup>3</sup> ) | 416.327  | 418.037   | 417.445  | 417.237   | 417.698  | 417.953  |
|                    | wt. (%)                 | 3.47     | 6.41      | 6.39     | 7.70      | 4.31     | 5.41     |
|                    | $R_p$ (%)               | 5.78     | 6.18      | 6.71     | 7.89      | 8.67     | 10.1     |
|                    | $R_{wp}$ (%)            | 6.93     | 7.11      | 7.70     | 8.72      | 8.61     | 9.03     |
|                    | $R_{exp}$ (%)           | 5.43     | 5.78      | 6.05     | 6.48      | 7.37     | 8.47     |
|                    | $\chi^2$                | 1.63     | 1.51      | 1.62     | 1.81      | 1.36     | 1.14     |

 $R_p$ : the profile factor;  $R_{wp}$ : weighted profile factor;  $R_{exp}$ : expected weighted profile factor;  $\chi^2$ : reduced chi-square

|                         |            |                   |           | Rond lon  | othe (nm) |           |           |  |
|-------------------------|------------|-------------------|-----------|-----------|-----------|-----------|-----------|--|
| polyhedron types        | Bond types | Bond lengths (pm) |           |           |           |           |           |  |
|                         |            | x = 0             | x = 0.025 | x = 0.05  | x = 0.075 | x = 0.15  | x = 0.25  |  |
|                         | Zn(1)-O(1) | 199.67600         | 200.41200 | 202.17500 | 200.02200 | 197.20600 | 198.76300 |  |
| $[Zn(1)O_4]$            | Zn(1)-O(1) | 200.06100         | 201.78500 | 200.85000 | 199.63200 | 200.32600 | 203.92600 |  |
| [ZII(1)O <sub>4</sub> ] | Zn(1)-O(2) | 192.03100         | 192.73500 | 194.33600 | 191.72400 | 194.15400 | 193.47300 |  |
|                         | Zn(1)-O(3) | 196.25200         | 196.12100 | 193.51200 | 194.42000 | 196.03400 | 198.39100 |  |
|                         | Zn(2)-O(2) | 199.35800         | 199.82300 | 199.70400 | 198.19000 | 199.95500 | 199.44700 |  |
| [7n(2)() ]              | Zn(2)-O(3) | 192.68500         | 190.94500 | 191.11900 | 192.23200 | 193.87200 | 192.63000 |  |
| $[Zn(2)O_4]$            | Zn(2)-O(4) | 200.50700         | 199.55200 | 197.25000 | 200.41100 | 198.44600 | 199.52200 |  |
|                         | Zn(2)-O(6) | 198.72000         | 200.61500 | 201.13400 | 201.97500 | 202.74500 | 203.64800 |  |
|                         | Zn(3)-O(5) | 195.12400         | 197.78700 | 196.20500 | 197.06300 | 196.70700 | 195.91000 |  |
| [7n(2)0]                | Zn(3)-O(5) | 198.76400         | 196.71500 | 197.53700 | 196.45300 | 196.01000 | 194.17000 |  |
| $[Zn(3)O_4]$            | Zn(3)-O(4) | 194.01100         | 195.02200 | 193.90700 | 196.92200 | 194.32400 | 193.54400 |  |
|                         | Zn(3)-O(6) | 197.07800         | 196.58700 | 199.54600 | 198.71600 | 197.23800 | 198.40100 |  |
|                         | B(1)-O(1)  | 130.49800         | 129.23800 | 130.54200 | 133.15100 | 129.58100 | 121.45100 |  |
| $[B(1)O_3]$             | B(1)-O(2)  | 137.67400         | 138.02000 | 134.40900 | 133.25900 | 137.47100 | 146.34900 |  |
|                         | B(1)-O(3)  | 136.32700         | 138.07400 | 139.80700 | 144.11500 | 136.59900 | 134.76600 |  |
|                         | B(2)-O(4)  | 133.75100         | 136.01400 | 135.02700 | 138.10300 | 135.11800 | 131.46000 |  |
| $[B(2)O_3]$             | B(2)-O(5)  | 137.57500         | 135.67700 | 139.77800 | 131.35100 | 134.22600 | 137.01600 |  |
|                         | B(2)-O(6)  | 138.19500         | 138.39300 | 134.44200 | 137.56500 | 141.10300 | 142.82900 |  |







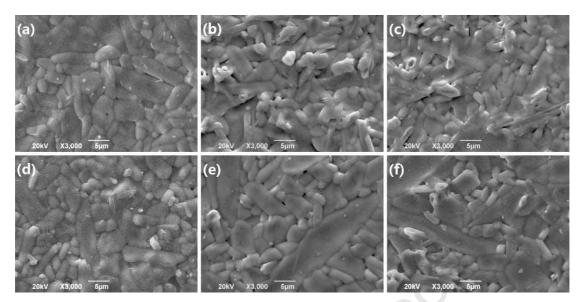


Fig.4

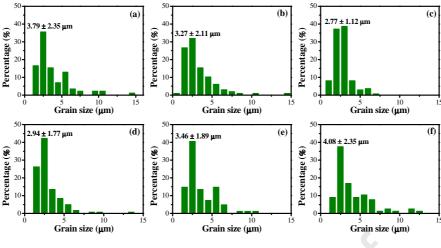
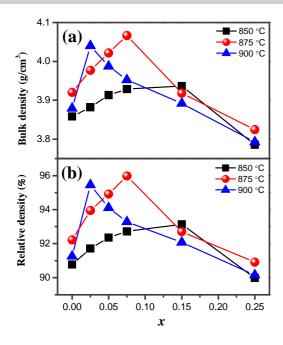
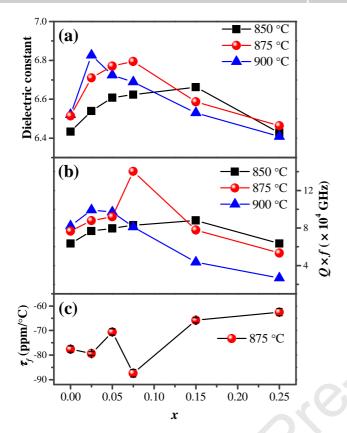
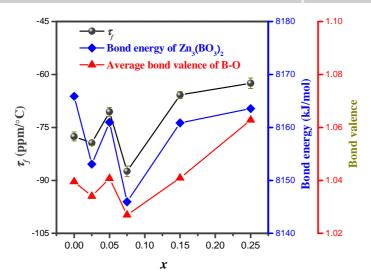


Fig.5







| Declaration of interests   |
|--|
| $\square$ The authors declare that they have no known competing financial interests or personal relationships that could have appeared to influence the work reported in this paper. |
| □The authors declare the following financial interests/personal relationships which may be considered as potential competing interests:  |
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